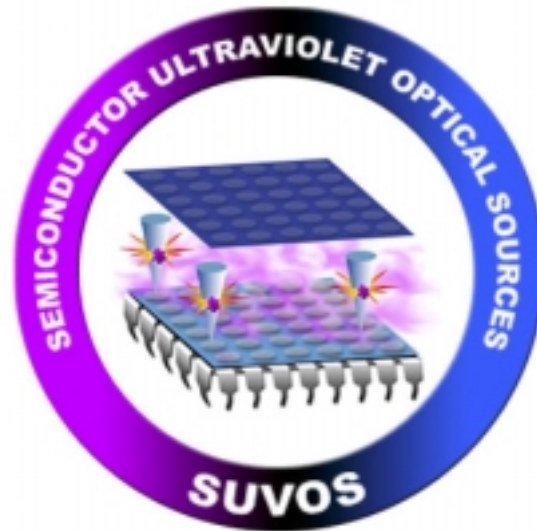


Semiconductor Ultraviolet Optical Sources



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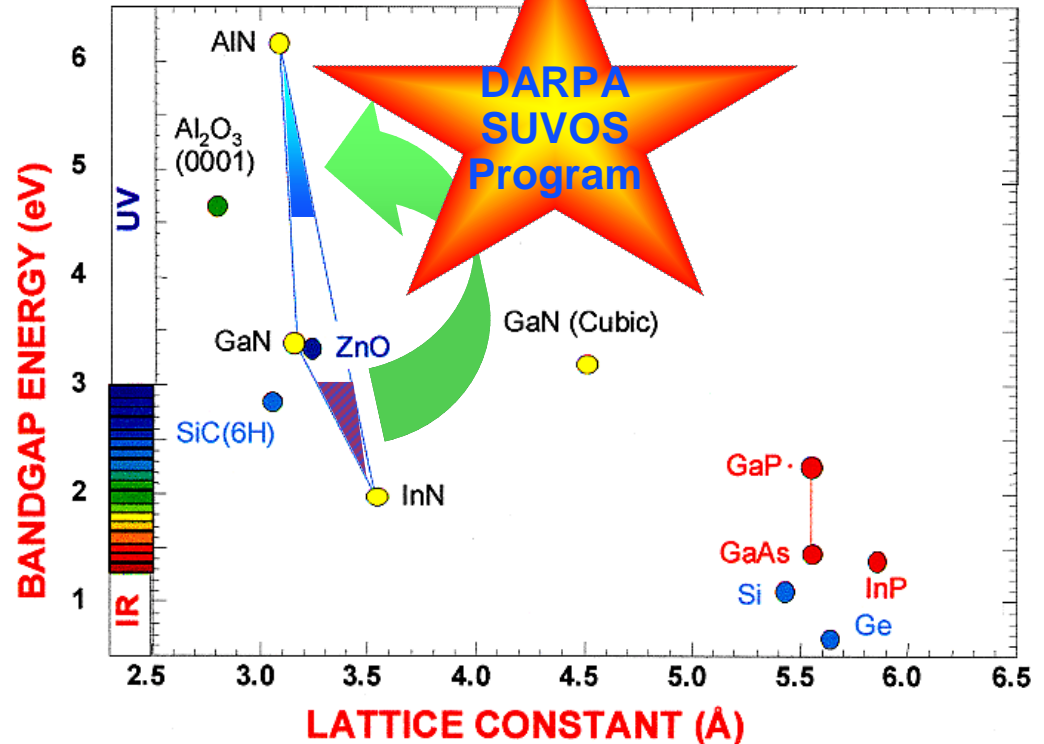
Wide Bandgap Photonics Technology

Program Goals:

- ❖ Demonstrate semiconductor UV optical sources ($\lambda = 280$ nm).
- ❖ Compared to current non-semiconductor approaches
 - Reduce power consumption by 50x
 - Reduce size/weight by >100x

Program Challenges:

- ❖ *p*-type conductivity of UV materials
- ❖ Device Innovation
 - Suppress non-radiative recombination
 - Epitaxial uniformity and strain management



Program Notes

- ❖ 48 month program (BAA 01-49)
 - Phase I (12-18 months) baseline effort
 - Phase II outyears as options
- ❖ Exit Criteria Phase I \Rightarrow Phase II
- ❖ Primary program focus
 - Optoelectronics
 - Spin-offs to bipolar electronics
- ❖ Bidders Brief 8 Nov, Austin TX



Technology Challenges

- ❖ ***p*-type Conductivity**
 - High Al content material
 - Ohmic contacts

- ❖ **Device Innovation**
 - Suppress non-radiative recombination
 - Strain management
 - Novel structures

- ❖ **Large Band Offsets**
 - Reduce turn-on voltage
 - Enhance carrier transport



Program Plan

❖ Task 1: UV Materials Development

- p -type doping (and ohmic contact development)
- Band-gap engineered heterostructures
- Suppress non-radiative recombination

❖ Task 2: Device Innovation

- 340 nm LED and Laser Diode (NADH)
- 280 nm LED (Amino Acids, Comms)

❖ Task 3: Integration and Demonstration

- Transceiver test bed
- Bio-detection test bed



Task 1: UV Materials Development

❖ Research Challenges:

- Improve p-type Conductivity
- Reduce Operating Voltage
- Enhance Radiative Efficiency
- Ohmic contact optimization



Task 2: Device Innovation

❖ Research Challenges:

- Novel structures
- Cavity Optimization
- Light Extraction through contact layers
- Uniformity and reproducibility
- Current Injection techniques
- Thermal Management
- Strain and Cracking



Task 3: Integration and Demonstration

❖ Research Challenges

- Transceiver test bed development
- Optical fluorescence test bed
- Heterogeneous Integration



Phase I Exit Criteria

- ❖ Operating wavelength
- ❖ Optical output power
- ❖ Quantum efficiency
- ❖ Operating voltage
- ❖ *p*-type high Al alloy material

